



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

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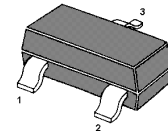
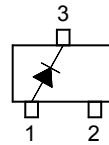
BAS116

Silicon Epitaxial Planar Diode

Low leakage switching diode

Features

- Plastic SMD package
- Low leakage current



Marking Code: **JV**
SOT-23 Plastic Package

Application

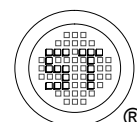
- Low leakage current applications in surface mounted circuits.

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	215	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	$t = 1\ \mu\text{s}$ 4	A
		$t = 1\ \text{ms}$ 1	
		$t = 1\ \text{s}$ 0.5	
Power Dissipation	P_{tot}	250	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage	V_F	0.9 1 1.1 1.25	V V V V
at $I_F = 1\ \text{mA}$			
at $I_F = 10\ \text{mA}$			
at $I_F = 50\ \text{mA}$			
at $I_F = 150\ \text{mA}$	V_F	1.25	V
Reverse Current	I_R	5 80	nA
at $V_R = 75\ \text{V}$			
at $V_R = 75\ \text{V}, T_j = 150\text{ }^\circ\text{C}$			
Diode Capacitance	C_d	2	pF
at $V_R = 0, f = 1\ \text{MHz}$			
Reverse Recovery Time	t_{rr}	3	μs
at $I_F = I_R = 10\ \text{mA}, R_L = 100\ \Omega, i_{Tr} = 0.1 I_R$			





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